

BF397 is PNP silicon transistor designed for high voltage applications.

TO-92F



CBE

### ABSOLUTE MAXIMUM RATINGS

|                                          |          |               |
|------------------------------------------|----------|---------------|
| Collector-Base Voltage                   | VCBO     | 90V           |
| Collector-Emitter Voltage                | VCEO     | 90V           |
| Emitter-Base Voltage                     | VEBO     | 6V            |
| Total Power Dissipation                  | Ptot     | 625mW         |
| Collector Current                        | IC       | 100mA         |
| Operating Junction & Storage Temperature | Tj, Tstg | -55 to +150°C |

### ELECTRICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER                            | SYMBOL   | MIN | MAX | UNIT | TEST CONDITIONS  |
|--------------------------------------|----------|-----|-----|------|------------------|
| Collector-Base Breakdown Voltage     | BVCBO    | 90  |     | V    | IC=10μA IE=0     |
| Collector-Emitter Breakdown Voltage  | BVCEO    | 90  |     | V    | IC=10mA IB=0     |
| Emitter-Base Breakdown Voltage       | BVEBO    | 6   |     | V    | IE=10μA IC=0     |
| Collector Cutoff Current             | ICBO     |     | 50  | nA   | VCB=70V IE=0     |
| Emitter Cutoff Current               | IEBO     |     | 50  | nA   | VEB=4V IC=0      |
| D.C. Current Gain                    | HFE      | 20  |     |      | IC=100μA VCE=10V |
|                                      |          | 25  |     |      | IC=1mA VCE=10V   |
|                                      |          | 40  | 250 |      | IC=10mA VCE=10V  |
|                                      |          | 20  |     |      | IC=100mA VCE=10V |
| Base-Emitter Saturation Voltage      | VBE(sat) |     | 0.9 | V    | IC=10mA IB=1mA   |
| Collector-Emitter Saturation Voltage | VCE(sat) |     | 0.5 | V    | IC=10mA IB=1mA   |